

**FEATURES**

High breakdown voltage

Marking: M

**2SA1179 (PNP)**

MAXIMUM RATINGS (TA=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	-55	V
Collector-Emitter Voltage	$V_{CEO}$	-50	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Collector Current -Continuous	$I_C$	-150	mA
Collector Power Dissipation	$P_C$	200	mW
Junction Temperature	$T_J$	150	°C
Storage Temperature	$T_{stg}$	-55 to +150	°C



ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{CBO}$	$I_C = -10\text{u A}, I_E = 0$	-55			V
Collector-emitter breakdown voltage	$V_{CEO}$	$I_C = -1\text{mA}, I_B = 0$	-50			V
Emitter-base breakdown voltage	$V_{EBO}$	$I_E = -10\text{ u A}, I_C = 0$	-5			V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -35\text{V}, I_E = 0$			-0.1	u A
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -4\text{V}, I_C = 0$			-0.1	u A
DC current gain	$h_{FE}$	$V_{CE} = -6\text{V}, I_C = -1\text{mA}$	200		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -50\text{mA}, I_B = -5\text{mA}$			-0.5	V
Base -emitter saturation voltage	$V_{BE(sat)}$	$I_C = -50\text{mA}, I_B = -5\text{mA}$			-1.0	V
Transition frequency	$f_T$	$V_{CE} = -6\text{V}, I_C = -10\text{mA}$		180		MHz
Collector output capacitance	$C_{ob}$	$V_{CB} = -6\text{V}, I_E = 0, f = 1\text{MHz}$		4		pF

**2SA1179** Typical Characteristics

